America Semiconductor

1N3671A thru 1N3673AR

Silicon Standard Recovery Diode

V_{RRM} = 50 V - 1000 V

I_F = 12 A

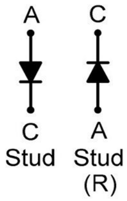
Features

- High Surge Capability
- Types up to 1000 V V_{RRM}

DO-4 Package

Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.



Maximum ratings, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	1N3671A (R)	1N3673A (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		800	1000	V
RMS reverse voltage	V_{RMS}		560	700	V
DC blocking voltage	V_{DC}		800	1000	V
Continuous forward current	I_F	$T_C \leq 150$ °C	12	12	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	T_C = 25 °C, t_p = 8.3 ms	240	240	A
Operating temperature	T_j		-65 to 200	-65 to 200	°C
Storage temperature	T_{stg}		-65 to 200	-65 to 200	°C

Electrical characteristics, at Tj = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	1N3671A (R)	1N3673A (R)	Unit
Diode forward voltage	V_F	I_F = 12 A, T_j = 25 °C	1.1	1.1	V
Reverse current	I_R	V_R = 50 V, T_j = 25 °C	10	10	µA
		V_R = 50 V, T_j = 175 °C	15	15	mA
Thermal characteristics					
Thermal resistance, junction - case	R_{thJC}		2.00	2.00	°C/W

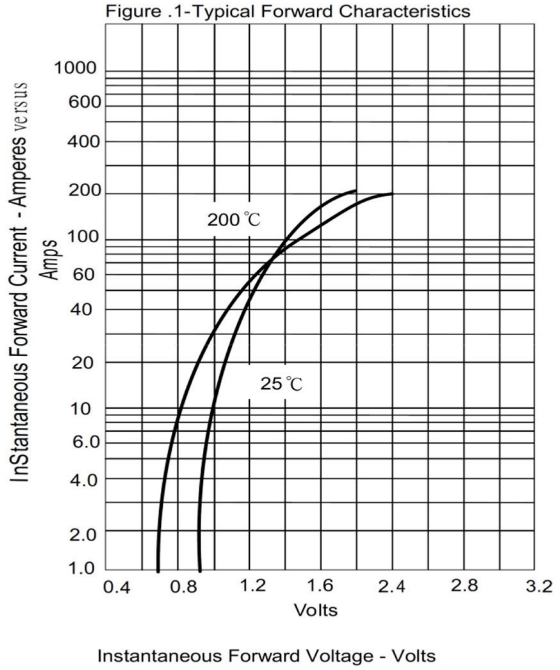


Figure .1-Typical Forward Characteristics

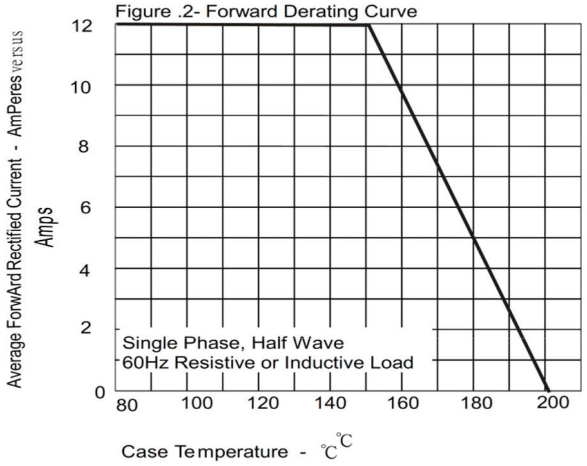


Figure .2- Forward Derating Curve

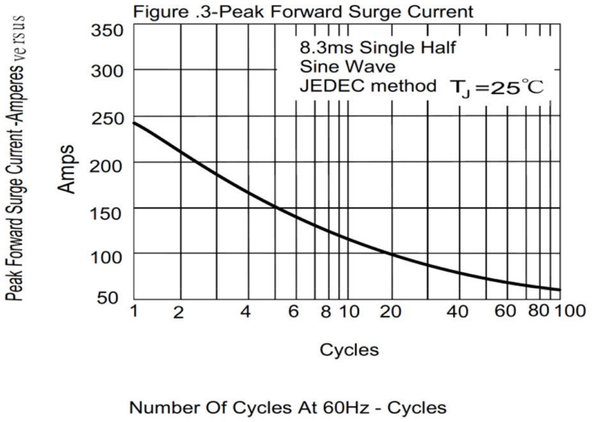


Figure .3-Peak Forward Surge Current

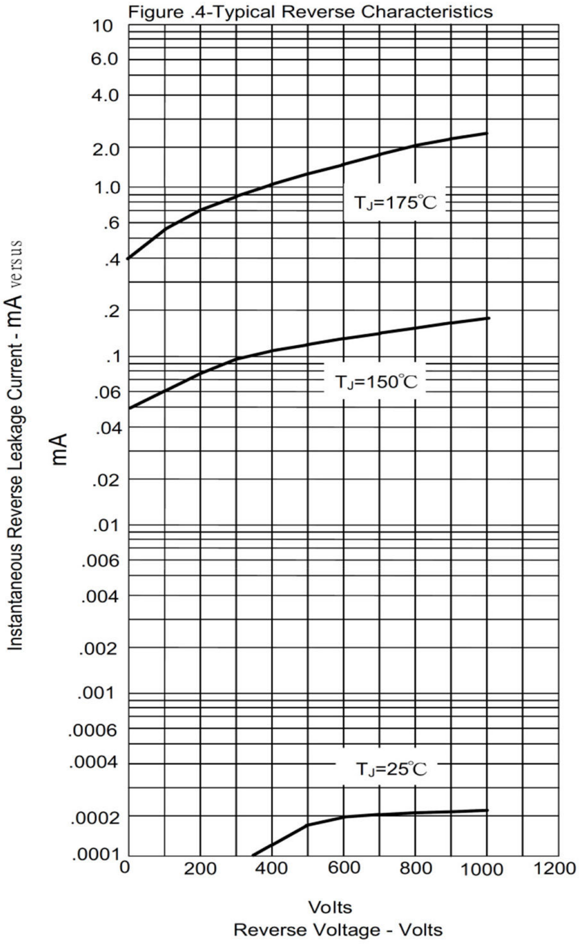


Figure .4-Typical Reverse Characteristics